

Electrostatic embedding for solid-state excited-state calculations: an application to two-dimensional transition metal dichalcogenides

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ABSTRACT

Due to the high computational cost still associated to excited-state calculations at the solid-state, electrostatic embedding schemes combined to TD-DFT appear as an attractive alternative for the accurate modeling of the photophysical properties of materials at low computational cost [1]. In particular, approaches devised to reproduce the exact Coulomb potential of an infinite periodic crystal with a large array of fitted point charges, such as the Self-Consistent Ewald (SC-Ewald) approach, have been proposed and successfully applied to various complex systems and processes [2, 1], and later extended to materials with reduced periodicities [3].

In this contribution, we present application of such an approach to the modeling of the UV-Vis. simulation of a series of two-dimensional transition metal dichalcogenides materials with reduced periodicities, in view of their importance in optoelectronic applications.

References

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